Hitoshi Habuka

List of Publications by Year
in descending order

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156 papers	1,311 citations	17 h-index	26 g-index
		471509	552781

156 all docs	156 docs citations	156 times ranked	362 citing authors

#	Article	IF	Citations
1	Anticorrosive Behavior of Aluminum Nitride Surface Exposed to Chlorine Trifluoride Gas at High Temperatures. ECS Journal of Solid State Science and Technology, 2021, 10, 034006.	1.8	0
2	Boron-Silicon Film Chemical Vapor Deposition Using Boron Trichloride, Dichlorosilane and Monomethylsilane Gases. ECS Journal of Solid State Science and Technology, 2021, 10, 064006.	1.8	4
3	Chemical Conditions of SiCNO Film Exposed to ClF₃ Gas. ECS Journal of Solid State Science and Technology, 2021, 10, 103004.	1.8	0
4	Benzoxazine-modified BMI Heat-resistant Resin with Low Dielectric Properties. Transactions of the Japan Institute of Electronics Packaging, 2021, 14, E20-016-1-E20-016-14.	0.4	2
5	Deposition and etching behaviour of boron trichloride gas at silicon surface. Journal of Crystal Growth, 2020, 529, 125301.	1.5	6
6	Quartz crystal microbalance for real-time monitoring chlorosilane gas transport in slim vertical cold wall chemical vapor deposition reactor. Materials Science in Semiconductor Processing, 2020, 106, 104759.	4.0	2
7	Side wall water outlet design for silicon wafer wet cleaning bath. Materials Science in Semiconductor Processing, 2020, 110, 104970.	4.0	1
8	Electric Current in Rate Equation for Parallel Plate Plasma-Enhanced Chemical Vapour Deposition of SiC x N y O z Film without Heat Assistance. ECS Journal of Solid State Science and Technology, 2020, 9, 024017.	1.8	2
9	Anticorrosive Behavior of SiC x N y O z Film Formed by Non-Heat Assistance Plasma-Enhanced Chemical Vapor Deposition Using Monomethylsilane, Nitrogen and Argon Gases. ECS Journal of Solid State Science and Technology, 2020, 9, 024001.	1.8	4
10	Temperature Influence on Organic Molecular Interaction on Silicon Oxide Surface In Situ Measured Utilizing a Quartz Crystal Microbalance. ECS Journal of Solid State Science and Technology, 2020, 9, 104007.	1.8	1
11	Design of a Silicon Carbide Chemical Vapor Deposition Reactor Cleaning Process Using Chlorine Trifluoride Gas Accounting for Exothermic Reaction Heat. ECS Journal of Solid State Science and Technology, 2020, 9, 104008.	1.8	4
12	High-Temperature Reactor Cleaning Using Chlorine Trifluoride Gas for Silicon Carbide Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2019, 8, P400-P406.	1.8	4
13	Influence of Metal and Polymer Substrate on SiC<i>_x</i>N<i>_y</i>O<i>_z</i> Film Formation by Non-Heat Assistance Plasma-Enhanced Chemical Vapor Deposition Using Monomethylsilane, Nitrogen and Argon Gases. ECS Journal of Solid State Science and Technology, 2019, 8, P407-P411.	1.8	3
14	Exposure of Tantalum Carbide, Silicon Nitride and Aluminum Nitride to Chlorine Trifluoride Gas. ECS Journal of Solid State Science and Technology, 2019, 8, P175-P179.	1.8	7
15	Behavior of Viscous Liquid Byproduct Formed in Exhaust Tube by Silicon Carbide Epitaxial Growth. ECS Journal of Solid State Science and Technology, 2019, 8, P805-P810.	1.8	1
16	Silicon Epitaxial Reactor for Minimal Fab. , 2018, , .		0
17	Real time evaluation of silicon epitaxial growth process by exhaust gas measurement using quartz crystal microbalance. Materials Science in Semiconductor Processing, 2018, 88, 192-197.	4.0	6
18	Water Outlet Design of Wet Cleaning Bath for 300-mm Diameter Silicon Wafers. ECS Journal of Solid State Science and Technology, 2018, 7, N123-N127.	1.8	3

#	ARTICLE	IF	CITATIONS
19	Silicon epitaxial growth accelerated by parallel Langmuir processes using SiH2Cl2 and SiH3CH3 gases. Semiconductor Science and Technology, 2018, 33, 094002.	2.0	2
20	Advantages of a slim vertical gas channel at high SiHCl3 concentrations for atmospheric pressure silicon epitaxial growth. Materials Science in Semiconductor Processing, 2018, 87, 13-18.	4.0	10
21	Yttrium oxide film for protecting quartz glass surface from etching by long-term exposure to chlorine trifluoride gas at room temperature. Materials Science in Semiconductor Processing, 2018, 83, 211-215.	4.0	5
22	Increase in silicon film deposition rate in a SiHCl3-SiHx-H2 system. Journal of Crystal Growth, 2017, 468, 204-207.	1.5	8
23	Susceptor Coating Materials Applicable for SiC Reactor Cleaning. Materials Science Forum, 2017, 897, 99-102.	0.3	9
24	Transport phenomena in a slim vertical atmospheric pressure chemical vapor deposition reactor utilizing natural convection. Materials Science in Semiconductor Processing, 2017, 71, 348-351.	4.0	6
25	Parallel langmuir processes for silicon epitaxial growth in a SiHCl 3 -SiH x -H 2 system. Materials Science in Semiconductor Processing, 2017, 72, 134-138.	4.0	5
26	Non-Heat Assistance Plasma-Enhanced Chemical Vapor Deposition of SiCxNyOzFilm Using Monomethylsilane, Nitrogen and Argon. ECS Journal of Solid State Science and Technology, 2017, 6, P443-P448.	1.8	6
27	Mirror Etching of Single Crystalline C-Face 4H-Silicon Carbide Wafer by Chlorine Trifluoride Gas. ECS Journal of Solid State Science and Technology, 2017, 6, P582-P585.	1.8	7
28	Quick Cleaning Process for Silicon Carbide Chemical Vapor Deposition Reactor. ECS Journal of Solid State Science and Technology, 2017, 6, P526-P530.	1.8	12
29	Reflector Influence on Rapid Heating of Minimal Manufacturing Chemical Vapor Deposition Reactor. ECS Journal of Solid State Science and Technology, 2016, 5, P280-P284.	1.8	7
30	In Situ Measurement for Evaluating Temperature Change Related to Silicon Film Formation in a SiHCl₃-H₂System. ECS Journal of Solid State Science and Technology, 2016, 5, P16-P20.	1.8	5
31	Formation and Removal of Carbon Film on Silicon Carbide Surface Using Chlorine Trifluoride Gas. ECS Journal of Solid State Science and Technology, 2016, 5, P441-P445.	1.8	4
32	Repetition of In Situ Cleaning Using Chlorine Trifluoride Gas for Silicon Carbide Epitaxial Reactor. ECS Journal of Solid State Science and Technology, 2016, 5, P12-P15.	1.8	14
33	Non-heat assistance chemical vapor deposition of amorphous silicon carbide using monomethylsilane gas under argon plasma. Surface and Coatings Technology, 2016, 285, 255-261.	4.8	10
34	Slim Water Injection Nozzle for Silicon Wafer Wet Cleaning Bath. Advances in Chemical Engineering and Science, 2016, 06, 345-354.	0.5	6
35	Numerical evaluation of silicon epitaxial growth on a 450â€‰mm diameter substrate. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1539-1543.	1.8	3
36	<i>Inâ€situ</i> observation of chemical vapor deposition using SiHCl₃ and BCl₃ gases. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 953-957.	0.8	4

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37	By-Product Formation in a Trichlorosilane-Hydrogen System for Silicon Film Deposition. ECS Journal of Solid State Science and Technology, 2015, 4, P16-P19.	1.8	13
38	Surface and gas phase reactions induced in a trichlorosilaneâ€“SiH x system for silicon film deposition. Surface and Coatings Technology, 2015, 272, 273-277.	4.8	5
39	In Situ Cleaning Process of Silicon Carbide Epitaxial Reactor. ECS Journal of Solid State Science and Technology, 2015, 4, P137-P140.	1.8	16
40	Evaluation of Molecular Interaction between Organic Molecules Physisorbed on Silicon Native Oxide Surface in Dry and Humid Atmosphere. ECS Journal of Solid State Science and Technology, 2015, 4, P86-P90.	1.8	4
41	Cleaning Process for Using Chlorine Trifluoride Gas Silicon Carbide Chemical Vapor Deposition Reactor. Materials Science Forum, 2015, 821-823, 125-128.	0.3	3
42	In Situ Method for Determining Combination of Organic Compounds Interacting with Each Other on Silicon Oxide Surface. ECS Journal of Solid State Science and Technology, 2015, 4, P408-P414.	1.8	1
43	Metal Fluorides Produced Using Chlorine Trifluoride Gas. Journal of Surface Engineered Materials and Advanced Technology, 2015, 05, 228-236.	0.2	12
44	Cleaning Process Applicable to Silicon Carbide Chemical Vapor Deposition Reactor. ECS Journal of Solid State Science and Technology, 2014, 3, N3006-N3009.	1.8	14
45	Off-Orientation Influence on C-Face (0001) 4H-SiC Surface Morphology Produced by Etching Using Chlorine Trifluoride Gas. Materials Science Forum, 2014, 778-780, 734-737.	0.3	0
46	Precipitates formed in silicon wafers by prolonged high-temperature annealing in nitrogen atmosphere. Japanese Journal of Applied Physics, 2014, 53, 05FJ05.	1.5	2
47	Low temperature amorphous silicon carbide thin film formation process on aluminum surface using monomethylsilane gas and trichlorosilane gas. Journal of Crystal Growth, 2014, 401, 523-526.	1.5	1
48	Precipitates Caused in Silicon Wafers by Prolonged High-Temperature Annealing in Nitrogen Atmosphere. Materials Research Society Symposia Proceedings, 2014, 1591, 1.	0.1	0
49	Room Temperature and Reduced Pressure Chemical Vapor Deposition of Silicon Carbide on Various Materials Surface. Advances in Chemical Engineering and Science, 2014, 04, 389-395.	0.5	1
50	Langasite crystal microbalance frequency behavior over wide gas phase conditions for chemical vapor deposition. Surface and Coatings Technology, 2013, 230, 312-315.	4.8	9
51	Silicon Chemical Vapor Deposition Process Using a Half-Inch Silicon Wafer for Minimal Manufacturing System. Physics Procedia, 2013, 46, 230-238.	1.2	9
52	Precipitates caused by prolonged high-temperature annealing in floating zone silicon wafer grown from Czochralski single-crystal rod. Materials Science in Semiconductor Processing, 2013, 16, 923-927.	4.0	3
53	Chemical vapor deposition of amorphous silicon carbide thin films on metal surfaces using monomethylsilane gas at low temperatures. Surface and Coatings Technology, 2013, 217, 88-93.	4.8	11
54	Crystalline Defects in Silicon Wafer Caused by Prolonged High-Temperature Annealing in Nitrogen Atmosphere. Advanced Materials Research, 2013, 699, 445-449.	0.3	0

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55	Off-Orientation Influence on C-Face (0001) 4H-SiC Surface Morphology Produced by Etching Using Chlorine Trifluoride Gas. ECS Journal of Solid State Science and Technology, 2013, 2, N3025-N3027.	1.8	2
56	Surface Chemical Reaction Model of Silicon Dioxide Film Etching by Dilute Hydrogen Fluoride Using a Single Wafer Wet Etcher. ECS Journal of Solid State Science and Technology, 2013, 2, P264-P267.	1.8	11
57	Langasite Crystal Microbalance Used for In-Situ Monitoring of Amorphous Silicon Carbide Film Deposition. ECS Journal of Solid State Science and Technology, 2012, 1, P62-P65.	1.8	7
58	Room Temperature Process for Chemical Vapor Deposition of Amorphous Silicon Carbide Thin Film Using Monomethylsilane Gas. Materials Research Society Symposia Proceedings, 2012, 1433, 83.	0.1	1
59	Silicon Epitaxial Growth Rate and Transport Phenomena in a Vertical Stacked-Type Multi-Wafer Reactor. Japanese Journal of Applied Physics, 2012, 51, 026701.	1.5	2
60	Density and Behavior of Etch Pits on C-Face 4H-SiC Surface Produced by ClF₃ Gas. Materials Science Forum, 2012, 717-720, 379-382.	0.3	6
61	Concentration of Three Organic Compounds Influencing each other on Silicon Surface. Solid State Phenomena, 2012, 187, 303-306.	0.3	0
62	Numerical calculation model of a single wafer wet etcher using a swinging nozzle. Materials Science in Semiconductor Processing, 2012, 15, 543-548.	4.0	9
63	Silicon Epitaxial Growth Rate and Transport Phenomena in a Vertical Stacked-Type Multi-Wafer Reactor. Japanese Journal of Applied Physics, 2012, 51, 026701.	1.5	0
64	Mechanism of Silicon Carbide Film Deposition at Room Temperature Using Monomethylsilane Gas. Journal of the Electrochemical Society, 2011, 158, H352.	2.9	11
65	Low Temperature SiC Film Deposition Using Trichlorosilane Gas and Monomethylsilane Gas. Journal of Nanoscience and Nanotechnology, 2011, 11, 8374-8377.	0.9	3
66	Room temperature process for chemical vapor deposition of amorphous silicon carbide thin film using monomethylsilane gas. Surface and Coatings Technology, 2011, 206, 1503-1506.	4.8	8
67	Silicon epitaxial growth process using trichlorosilane gas in a single-wafer high-speed substrate rotation reactor. Journal of Crystal Growth, 2011, 327, 1-5.	1.5	29
68	Langasite Crystal Microbalance for Development of Reactive Surface Preparation of Silicon Carbide Film Deposition from Monomethylsilane Gas. Japanese Journal of Applied Physics, 2011, 50, 096505.	1.5	5
69	Silicon Surface Morphology after Annealing in Ambient Hydrogen Containing a Trace Amount of Hydrogen Halide Gas. Japanese Journal of Applied Physics, 2011, 50, 025701.	1.5	0
70	Water Motion over a Wafer Surface Rotating in a Single-Wafer Wet Cleaner. ECS Transactions, 2011, 41, 279-286.	0.5	2
71	Water Motion over a Wafer Surface Rotating in a Single-Water Wet Cleaner. Journal of the Electrochemical Society, 2011, 158, H487.	2.9	13
72	Langasite Crystal Microbalance for Development of Reactive Surface Preparation of Silicon Carbide Film Deposition from Monomethylsilane Gas. Japanese Journal of Applied Physics, 2011, 50, 096505.	1.5	2

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73	Advance of Atomic Layer Deposition in Semiconductor Materials Manufacturing Process: Cleaning Technology for Thin Film Formation Reactor. Journal of the Vacuum Society of Japan, 2011, 54, 97-104.	0.3	0
74	Silicon Surface Morphology after Annealing in Ambient Hydrogen Containing a Trace Amount of Hydrogen Halide Gas. Japanese Journal of Applied Physics, 2011, 50, 025701.	1.5	0
75	Silicon carbide film deposition at low temperatures using monomethylsilane gas. Surface and Coatings Technology, 2010, 204, 1432-1437.	4.8	18
76	Dominant Forces for Driving Bubbles in a Wet Cleaning Bath Using Megasonic Wave. Journal of the Electrochemical Society, 2010, 157, H585.	2.9	13
77	Molecular Interaction Radii and Rate Constants for Clarifying Organic Compound Physisorption on Silicon Surface. Journal of the Electrochemical Society, 2010, 157, H1014.	2.9	11
78	4H-SiC Surface Morphology Etched Using ClF₃ Gas. Materials Science Forum, 2010, 645-648, 787-790.	0.3	9
79	Temperature-Dependent Behavior of 4H-Silicon Carbide Surface Morphology Etched Using Chlorine Trifluoride Gas. Journal of the Electrochemical Society, 2009, 156, H971.	2.9	27
80	Hafnium Oxide Film Etching Using Hydrogen Chloride Gas. Japanese Journal of Applied Physics, 2009, 48, 125503.	1.5	2
81	Etching Rate of Silicon Dioxide Using Chlorine Trifluoride Gas. Japanese Journal of Applied Physics, 2009, 48, 026504.	1.5	10
82	Water and Bubble Motions Under Megasonic Wave in a Silicon Wafer Wet Cleaning Bath. ECS Transactions, 2009, 25, 265-272.	0.5	3
83	Hafnium Oxide Etching Using Hydrogen Chloride Gas. ECS Transactions, 2009, 19, 289-299.	0.5	1
84	Atomospheric Pressure SiC Film Deposition at Low Temperatures Using SiH₃CH₃ and HCl Gases. ECS Transactions, 2009, 25, 191-198.	0.5	1
85	Etching Rate Behavior of 4H-Silicon Carbide Using Chlorine Trifloride Gas. ECS Transactions, 2008, 13, 39-52.	0.5	8
86	Heat Transport and Temperature Gradient in Silicon-on-Insulator Wafer during Flash Lamp Annealing Process. Japanese Journal of Applied Physics, 2008, 47, 6277-6281.	1.5	2
87	Decarbonation and Pore Structural Change of Ca-Solid Reactant for CaO/CO2 Chemical Heat Pump. Journal of Chemical Engineering of Japan, 2008, 41, 513-518.	0.6	5
88	Water Motion in a Water Curtain Head for Cleaning a Large Glass Plate. Japanese Journal of Applied Physics, 2007, 46, 838-842.	1.5	0
89	Determination of Etch Rate Behavior of 4Hâ€“SiC Using Chlorine Trifluoride Gas. Japanese Journal of Applied Physics, 2007, 46, 7875.	1.5	24
90	Heat Transport Analysis for Flash Lamp Annealing. Japanese Journal of Applied Physics, 2007, 46, 937-942.	1.5	22

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91	In-Situ Measurement Method and Rate Theory for Clarifying Multi-Component Organic Compounds Adsorption and Desorption on Silicon Surface. ECS Transactions, 2007, 11, 363-374.	0.5	1
92	Physisorption and Desorption of Diethyl Phthalate and Isopropanol on a Silicon Surface. Journal of the Electrochemical Society, 2007, 154, H1031.	2.9	9
93	Carbonation/Decarbonation of Ca-Solid Reactant Derived from Natural Limestone for Thermal-Energy Storage and Temperature Upgrade. Journal of Chemical Engineering of Japan, 2007, 40, 1270-1274.	0.6	2
94	Polycrystalline silicon carbide film deposition using monomethylsilane and hydrogen chloride gases. Journal of Crystal Growth, 2007, 300, 374-381.	1.5	18
95	Etch rate and surface morphology of polycrystalline Î²-silicon carbide using chlorine trifluoride gas. Thin Solid Films, 2006, 514, 193-197.	1.8	12
96	Small-Batch Reactor Development for Silicon Epitaxial Film Growth Based on Theory of Transport Phenomena. ECS Transactions, 2006, 2, 21-32.	0.5	2
97	Dominant rate process of silicon surface etching by hydrogen chloride gas. Thin Solid Films, 2005, 489, 104-110.	1.8	35
98	Gas Velocity Influence on Silicon Surface Organic Contamination Evaluated Using Quartz Crystal Microbalance. Journal of the Electrochemical Society, 2005, 152, G862.	2.9	9
99	Silicon Carbide Etching Using Chlorine Trifluoride Gas. Japanese Journal of Applied Physics, 2005, 44, 1376-1381.	1.5	32
100	Quartz Crystal Microbalance for Silicon Surface Organic Contamination. Journal of the Electrochemical Society, 2005, 152, G241.	2.9	12
101	Highly Concentrated Ozone Gas for Preparing Wettable Polyimide Surface. Japanese Journal of Applied Physics, 2005, 44, 5225-5230.	1.5	3
102	Air Flow in Square Quartz Plate Spin Cleaner. Japanese Journal of Applied Physics, 2005, 44, 8182-8185.	1.5	2
103	Heat Balance Evaluation for Rapid Thermal Processing System Design. Journal of the Electrochemical Society, 2005, 152, G924.	2.9	5
104	A Practical Design Method for a Rapid Thermal Processing System. Japanese Journal of Applied Physics, 2004, 43, 833-838.	1.5	1
105	Room Temperature Halogenation of Polyimide Film Surface using Chlorine Trifluoride Gas. Japanese Journal of Applied Physics, 2004, 43, 730-734.	1.5	1
106	Water Motion in Carrierless Wet Station. Journal of the Electrochemical Society, 2004, 151, G814.	2.9	10
107	Silicon Etch Rate Using Chlorine Trifluoride. Journal of the Electrochemical Society, 2004, 151, G783.	2.9	17
108	Formation mechanism of local thickness profile of silicon epitaxial film. Journal of Crystal Growth, 2004, 266, 327-332.	1.5	8

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109	Airborne Organic Contamination Behavior on Silicon Wafer Surface. Journal of the Electrochemical Society, 2003, 150, G148.	2.9	24
110	High-Performance Silicon Etching Using Chlorine Trifluoride Gas. Journal of the Electrochemical Society, 2003, 150, G461.	2.9	15
111	Time-Dependent Airborne Organic Contamination on Silicon Wafer Surface Stored in a Plastic Box. Japanese Journal of Applied Physics, 2003, 42, 1575-1580.	1.5	15
112	Flatness Deterioration of Silicon Epitaxial Film Formed in a Horizontal Single-Wafer Epitaxial Reactor II. Japanese Journal of Applied Physics, 2002, 41, 5692-5696.	1.5	6
113	Model of boron incorporation into silicon epitaxial film in a B2H6â€“SiHCl3â€“H2 system. Journal of Crystal Growth, 2001, 222, 183-193.	1.5	6
114	Hot-wall and cold-wall environments for silicon epitaxial film growth. Journal of Crystal Growth, 2001, 223, 145-155.	1.5	5
115	Design of a Rapid Thermal Processing System Using a Reflection-Resolved Ray Tracing Method. Journal of the Electrochemical Society, 2001, 148, G543.	2.9	8
116	Development of Evaluation Method for Organic Contamination on Silicon Wafer Surfaces. Journal of the Electrochemical Society, 2001, 148, G644.	2.9	20
117	Adsorption and Desorption Rate of Multicomponent Organic Species on Silicon Wafer Surface. Journal of the Electrochemical Society, 2001, 148, G365.	2.9	33
118	Nonempirical Design of Rapid Thermal Processing System. Japanese Journal of Applied Physics, 2001, 40, 7123-7128.	1.5	4
119	Flatness Deterioration of Silicon Epitaxial Film Formed Using Horizontal Single-Wafer Epitaxial Reactor. Japanese Journal of Applied Physics, 2001, 40, 6041-6044.	1.5	7
120	CVD Material Processing. Numerical Calculations of Heat Profile using Circular Infrared Lamp Heating Furnace.. Kagaku Kogaku Ronbunshu, 2000, 26, 785-791.	0.3	2
121	Instability of diborane gas in silicon epitaxial film growth. Journal of Crystal Growth, 2000, 209, 807-815.	1.5	11
122	Rate Theory of Multicomponent Adsorption of Organic Species on Silicon Wafer Surface. Journal of the Electrochemical Society, 2000, 147, 2319.	2.9	30
123	Thermal Conditions in Rapid Thermal Processing System Using Circular Infrared Lamp. Journal of the Electrochemical Society, 2000, 147, 4660.	2.9	8
124	Dominant Overall Chemical Reaction in a Chlorine Trifluorideâ€“Siliconâ€“Nitrogen System at Atmospheric Pressure. Japanese Journal of Applied Physics, 1999, 38, 6466-6469.	1.5	9
125	A Direct Approach for Evaluating the Thermal Condition of a Silicon Substrate under Infrared Rays and Specular Reflectors. Journal of the Electrochemical Society, 1999, 146, 713-718.	2.9	14
126	Chemical process of silicon epitaxial growth in a SiHCl3â€“H2 system. Journal of Crystal Growth, 1999, 207, 77-86.	1.5	56

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127	In situ cleaning method for silicon surface using hydrogen fluoride gas and hydrogen chloride gas in a hydrogen ambient. Journal of Crystal Growth, 1998, 186, 104-112.	1.5	13
128	Reaction of Hydrogen Fluoride Gas at High Temperatures with Silicon Oxide Film and Silicon Surface. Japanese Journal of Applied Physics, 1998, 37, 6123-6127.	1.5	15
129	Change in Microroughness of a Silicon Surface during In Situ Cleaning Using HF and HCl Gases. Journal of the Electrochemical Society, 1998, 145, 4264-4271.	2.9	6
130	Haze Generation on Silicon Surface Heated in Hydrogen Ambient at Atmospheric Pressure. Journal of the Electrochemical Society, 1997, 144, 3261-3265.	2.9	6
131	Computation Transport Phenomena in Chemical Engineering. Transport of Dopant Gas during Silicon Epitaxial Thin-Film Growth in a Horizontal Reactor.. Kagaku Kogaku Ronbunshu, 1997, 23, 772-779.	0.3	3
132	Nonlinear increase in silicon epitaxial growth rate in a SiHCl3î—¸H2 system under atmospheric pressure. Journal of Crystal Growth, 1997, 182, 352-362.	1.5	32
133	Effect of Transport Phenomena on Boron Concentration Profiles in Silicon Epitaxial Wafers. Journal of the Electrochemical Society, 1996, 143, 677-682.	2.9	5
134	Model on transport phenomena and epitaxial growth of silicon thin film in SiHCl3î—¸H2 system under atmospheric pressure. Journal of Crystal Growth, 1996, 169, 61-72.	1.5	89
135	Gas flow and heat transfer in a pancake chemical vapor deposition reactor. Journal of Crystal Growth, 1995, 151, 375-383.	1.5	9
136	Roughness of Silicon Surface Heated in Hydrogen Ambient. Journal of the Electrochemical Society, 1995, 142, 3092-3098.	2.9	32
137	Modeling of Epitaxial Silicon Thinâ€Film Growth on a Rotating Substrate in a Horizontal Singleâ€Wafer Reactor. Journal of the Electrochemical Society, 1995, 142, 4272-4278.	2.9	37
138	Numerical Evaluation of Silicon-Thin Film Growth from SiHCl3-H2Gas Mixture in a Horizontal Chemical Vapor Deposition Reactor. Japanese Journal of Applied Physics, 1994, 33, 1977-1985.	1.5	20
139	4H Silicon Carbide Etching Using Chlorine Trifluoride Gas. Materials Science Forum, 0, 600-603, 655-658.	0.3	10
140	Low Temperature Chemical Vapour Deposition of Polycrystalline Silicon Carbide Film Using Monomethylsilane Gas. , 0, , .		0
141	Etch Pits on 4H-SiC Surface Produced by ClF₃ Gas. Materials Science Forum, 0, 679-680, 286-289.	0.3	2
142	Density of Etch Pits on C-Face 4H-SiC Surface Produced by ClF₃ Gas. Materials Science Forum, 0, 725, 49-52.	0.3	7
143	Amorphous Silicon Carbide Film Formation at Room Temperature by Monomethylsilane Gas. Materials Science Forum, 0, 740-742, 235-238.	0.3	0
144	Development of Silicon Carbide Dry Etcher Using Chlorine Trifluoride Gas. Materials Science Forum, 0, 778-780, 738-741.	0.3	7

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145	Chlorine Trifluoride Gas Transport and Etching Rate Distribution in Silicon Carbide Dry Etcher. Materials Science Forum, 0, 821-823, 553-556.	0.3	8
146	In Situ Observation of Chemical Vapour Deposition Using Langasite Crystal Microbalance. , 0, , .		0
147	A Method to Adjust Polycrystalline Silicon Carbide Etching Rate Profile by Chlorine Trifluoride Gas. Materials Science Forum, 0, 897, 383-386.	0.3	5
148	Quick and Practical Cleaning Process for Silicon Carbide Epitaxial Reactor. Materials Science Forum, 0, 924, 96-99.	0.3	0
149	4H-Silicon Carbide Wafer Surface after Chlorine Trifluoride Gas Etching. Materials Science Forum, 0, 924, 369-372.	0.3	1
150	High Temperature SiC Reactor Cleaning Using Chlorine Trifluoride Gas Achieved by Purified Pyrolytic Carbon Coating Film. Materials Science Forum, 0, 963, 141-145.	0.3	1
151	Chlorine Trifluoride Gas Distributor Design for Single-Crystalline C-Face 4H-Silicon Carbide Wafer Etcher. Materials Science Forum, 0, 963, 520-524.	0.3	3
152	Non-Plasma Dry Etcher Design for 200 mm-Diameter Silicon Carbide Wafer. Materials Science Forum, 0, 1004, 167-172.	0.3	1
153	Etching Rate Profile of C-Face 4H-SiC Wafer Depending on Total Gas Flow Rate of Chlorine Trifluoride and Nitrogen. Materials Science Forum, 0, 1004, 173-179.	0.3	2
154	Development of SiC Etching by Chlorine Fluoride Gas. Materials Science Forum, 0, 1004, 731-737.	0.3	1
155	SiC Epitaxial Reactor Cleaning by ClF₃ Gas with the Help of Reaction Heat. Materials Science Forum, 0, 1004, 186-192.	0.3	0
156	Water Flow Improvement by Pinhole Outlet in Batch-Type Wet Cleaning Bath for Large-Diameter Wafers. ECS Journal of Solid State Science and Technology, 0, , .	1.8	0